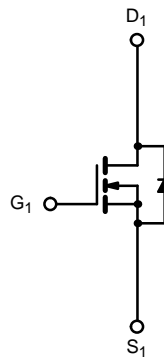
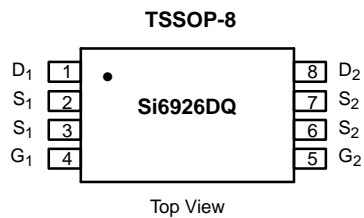




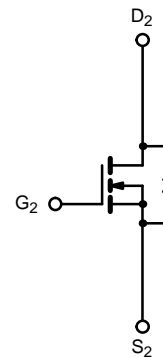
Dual N-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
20	0.035 @ $V_{GS} = 4.5$ V	± 4.0
	0.040 @ $V_{GS} = 3.0$ V	± 3.7
	0.045 @ $V_{GS} = 2.5$ V	± 3.5

TrenchFET[®]
Power MOSFETs
2.5-V Rated



N-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	± 4.0
		$T_A = 70^\circ\text{C}$	± 3.2
Pulsed Drain Current	I_{DM}	± 20	A
Continuous Source Current (Diode Conduction) ^a	I_S	1.25	
Maximum Power Dissipation ^a	P_D	$T_A = 25^\circ\text{C}$	1.0
		$T_A = 70^\circ\text{C}$	0.64
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	125	$^\circ\text{C/W}$

Notes

a. Surface Mounted on FR4 Board, $t \leq 10$ sec.



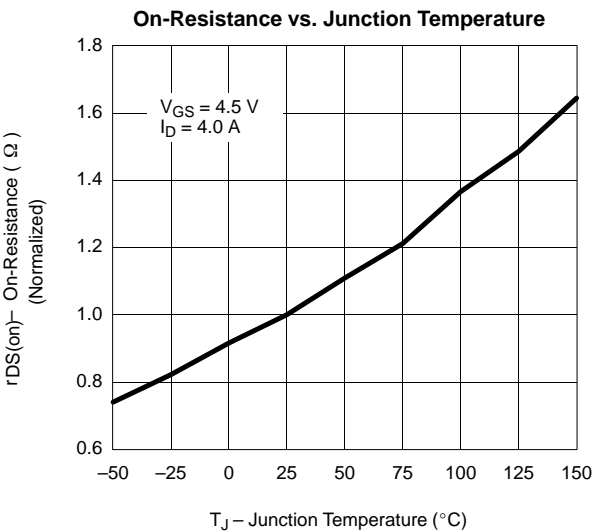
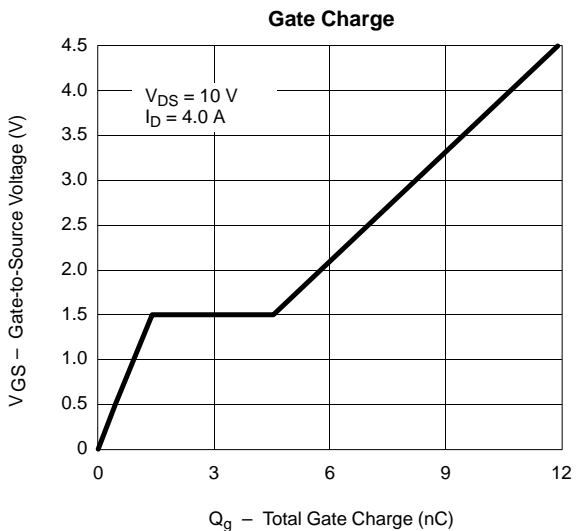
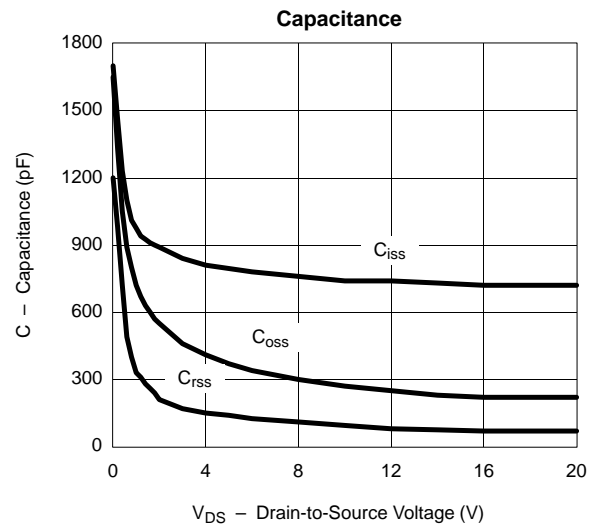
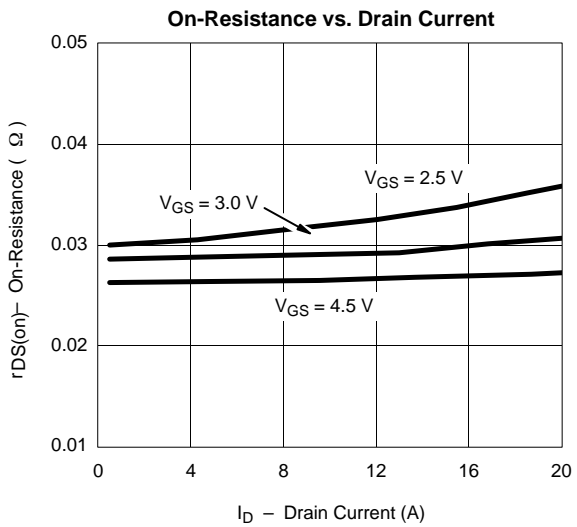
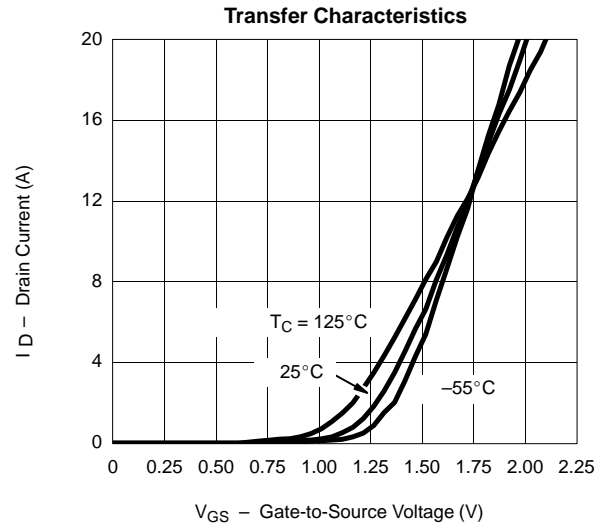
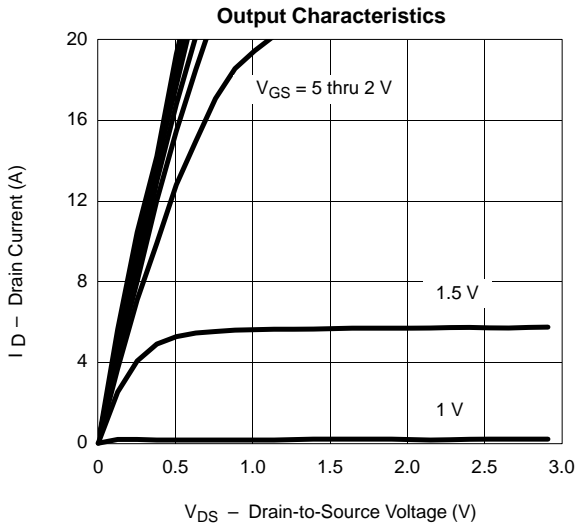
SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.5			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1	μA
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C			5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 5 V	10			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 4.5 V, I _D = 4.0 A		0.028	0.035	Ω
		V _{GS} = 3.0 V, I _D = 3.7 A		0.031	0.040	
		V _{GS} = 2.5 V, I _D = 3.5 A		0.033	0.045	
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 4.0 A		18		S
Diode Forward Voltage ^a	V _{SD}	I _S = 1.25 A, V _{GS} = 0 V		0.7	1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 4.0 A		12	20	nC
Gate-Source Charge	Q _{gs}			1.4		
Gate-Drain Charge	Q _{gd}			3.2		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 6 Ω I _D = 1 A, V _{GEN} = 10 V, R _G = 6 Ω		10	20	ns
Rise Time	t _r			30	50	
Turn-Off Delay Time	t _{d(off)}			60	80	
Fall Time	t _f			15	30	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.25 A, di/dt = 100 A/μs		50	90	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

